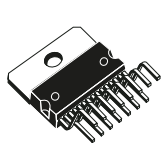
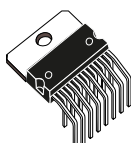


### 100 V, 100 W DMOS audio amplifier with mute/st-by

#### MULTIPOWER BCD TECHNOLOGY



Multiwatt15V



Multiwatt15H

#### Features

- Very high operating voltage range ( $\pm 40$  V)
- DMOS power stage
- High output power (up to 100 W music power)
- Muting/stand-by functions
- No switch on/off noise
- No boucherot cells
- Very low distortion
- Very low noise
- Short circuit protection
- Thermal shutdown

#### Description

The **TDA7294** is a monolithic integrated circuit in Multiwatt15 package, intended for use as audio class AB amplifier in Hi-Fi field applications (Home Stereo, self powered loudspeakers, Topclass TV). Thanks to the wide voltage range and to the high out current capability it is able to supply the highest power into both 4  $\Omega$  and 8  $\Omega$  loads even in presence of poor supply regulation, with high supply voltage rejection.

The built in muting function with turn on delay simplifies the remote operation avoiding switching on-off noises.

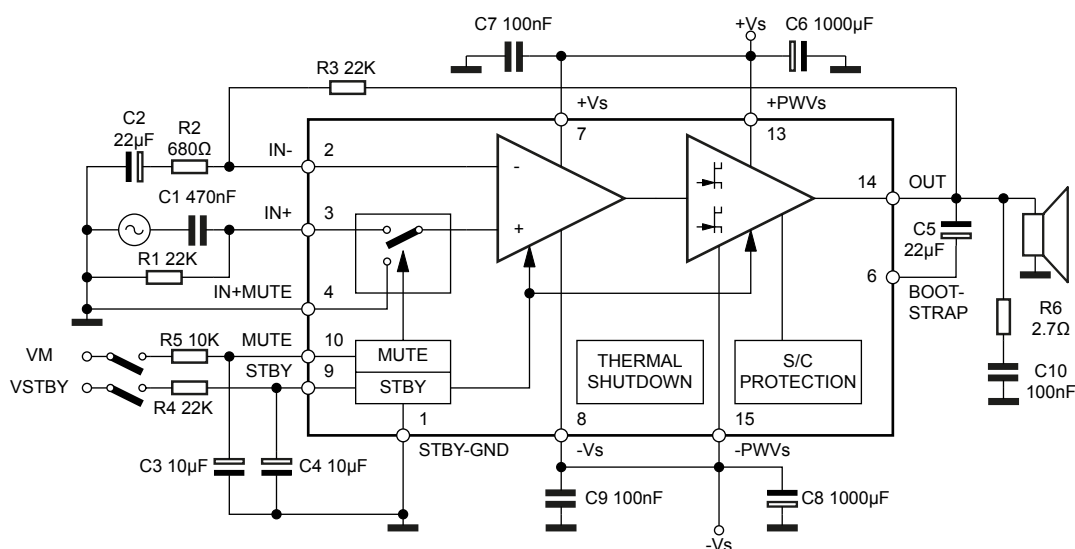
#### Maturity status link

[TDA7294](#)

| Order code | Package      |
|------------|--------------|
| TDA7294V   | Multiwatt15V |
| TDA7294HS  | Multiwatt15H |

# 1 Typical application

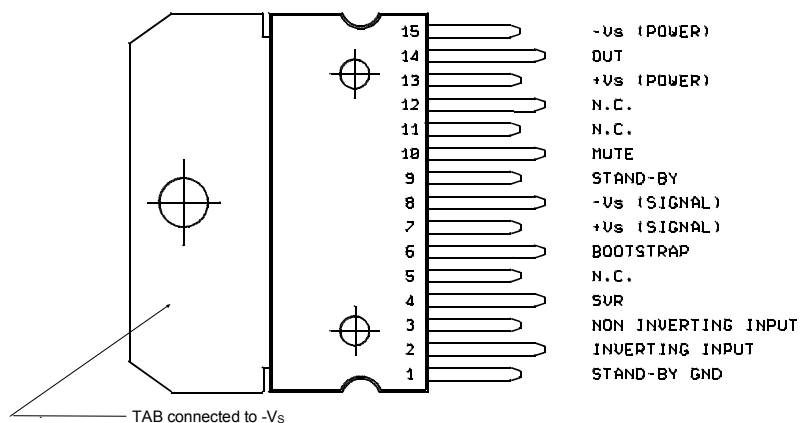
**Figure 1. Typical application and test circuit**



**Note:** The Boucherot cell R6, C10, normally not necessary for a stable operation it could be needed in presence of particular load impedances at  $V_S < \pm 25\text{ V}$ .

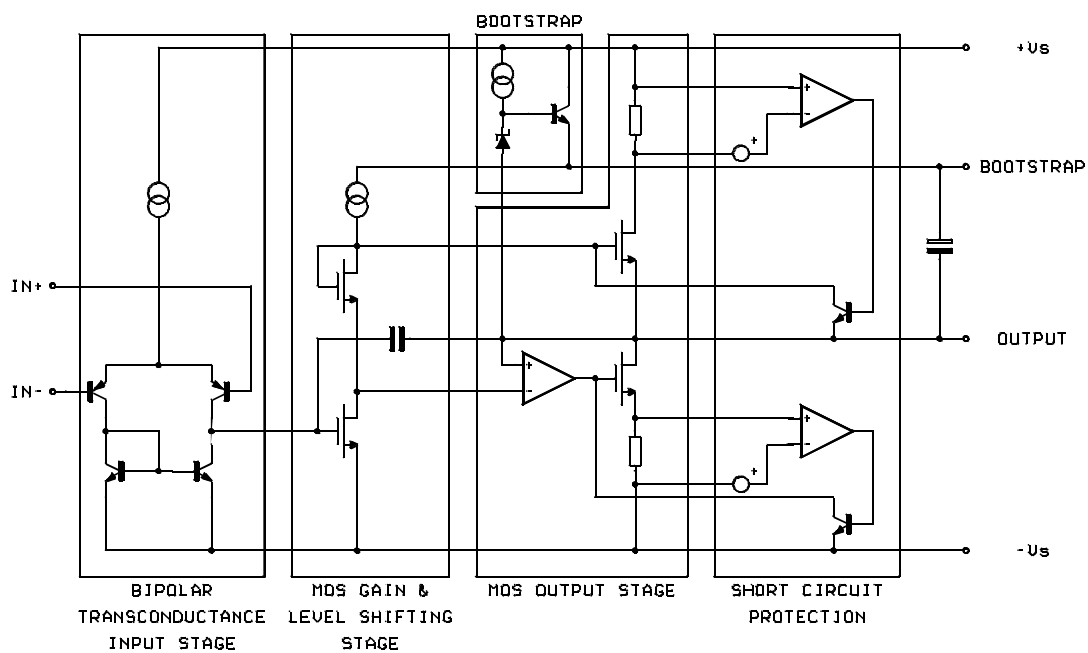
## 2 Pin connection

Figure 2. Pin connection (top view)



### 3 Block diagram

Figure 3. Block diagram



## 4 Maximum ratings

**Table 1. Absolute maximum ratings**

| Symbol    | Parameter                                                           | Value    | Unit               |
|-----------|---------------------------------------------------------------------|----------|--------------------|
| $V_S$     | Supply voltage (no signal)                                          | $\pm 50$ | V                  |
| $I_O$     | Output peak current                                                 | 10       | A                  |
| $P_{tot}$ | Total power dissipation ( $T_{case} = 70\text{ }^{\circ}\text{C}$ ) | 50       | W                  |
| $T_{op}$  | Operating ambient temperature range                                 | 0 to 70  | $^{\circ}\text{C}$ |
| $T_{stg}$ | Storage temperature                                                 | 150      | $^{\circ}\text{C}$ |
| $T_j$     | Junction temperature                                                |          |                    |

**Table 2. Thermal data**

| Symbol         | Parameter                        | Value | Unit                 |
|----------------|----------------------------------|-------|----------------------|
| $R_{th-jcase}$ | Thermal resistance junction-case | 1.5   | $^{\circ}\text{C/W}$ |

## 5 Electrical characteristics

Refer to the test circuit  $V_S = \pm 35\text{ V}$ ,  $R_L = 8\ \Omega$ ,  $G_V = 30\text{ dB}$ ;  $R_g = 50\ \Omega$ ;  $T_{\text{amb}} = 25\text{ }^\circ\text{C}$ ,  $f = 1\text{ kHz}$ ; unless otherwise specified.

**Table 3. Electrical characteristics**

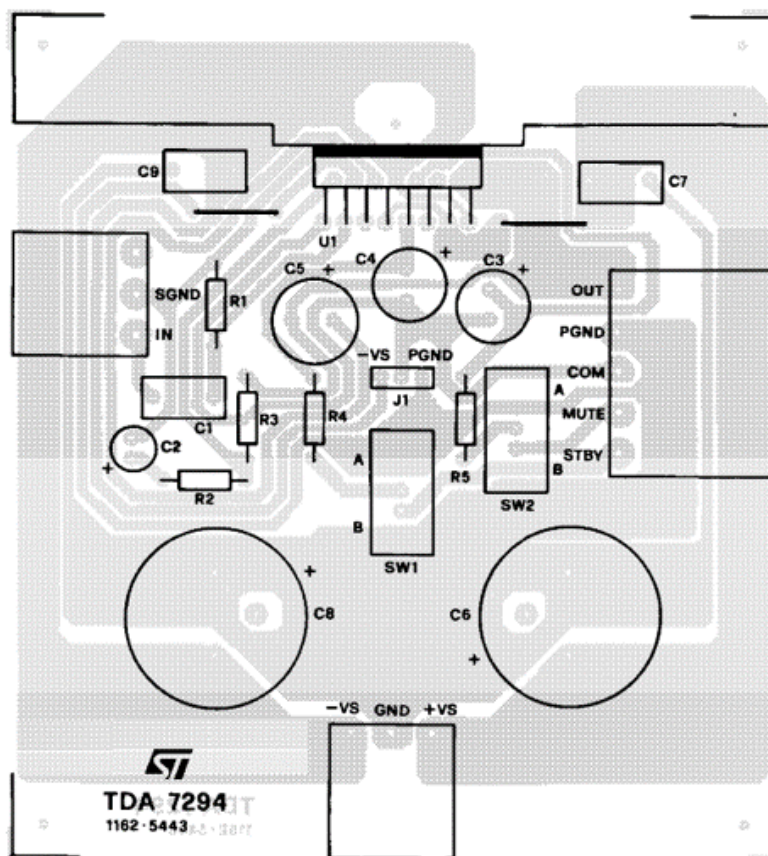
| Symbol                                                   | Parameter                                                                    | Test condition                                                          | Min.            | Typ.   | Max.      | Unit             |
|----------------------------------------------------------|------------------------------------------------------------------------------|-------------------------------------------------------------------------|-----------------|--------|-----------|------------------|
| $V_S$                                                    | Supply range                                                                 |                                                                         | 10              |        | 40        | V                |
| $I_q$                                                    | Quiescent current                                                            |                                                                         | 20              | 30     | 65        | mA               |
| $I_b$                                                    | Input bias current                                                           |                                                                         |                 |        | 500       | nA               |
| $V_{OS}$                                                 | Input offset voltage                                                         |                                                                         |                 |        | $\pm 10$  | mV               |
| $I_{OS}$                                                 | Input offset current                                                         |                                                                         |                 |        | $\pm 100$ | nA               |
| $P_O$                                                    | RMS continuous output power                                                  | $d = 0.5\%$ :                                                           |                 |        |           |                  |
|                                                          |                                                                              | $V_S = \pm 35\text{ V}$ , $R_L = 8\ \Omega$                             | 60              | 70     |           | W                |
|                                                          |                                                                              | $V_S = \pm 31\text{ V}$ , $R_L = 6\ \Omega$                             | 60              | 70     |           | W                |
|                                                          |                                                                              | $V_S = \pm 27\text{ V}$ , $R_L = 4\ \Omega$                             | 60              | 70     |           | W                |
|                                                          | Music Power (RMS)<br>IEC268.3 RULES - $\Delta t = 1\text{ s}$ <sup>(1)</sup> | $d = 10\%$                                                              |                 |        |           |                  |
|                                                          |                                                                              | $R_L = 8\ \Omega$ ; $V_S = \pm 38\text{ V}$                             |                 | 100    |           | W                |
|                                                          |                                                                              | $R_L = 6\ \Omega$ ; $V_S = \pm 33\text{ V}$                             |                 | 100    |           | W                |
|                                                          |                                                                              | $R_L = 4\ \Omega$ ; $V_S = \pm 29\text{ V}$ <sup>(2)</sup>              |                 | 100    |           | W                |
| d                                                        | Total harmonic distortion <sup>(3)</sup>                                     | $P_O = 5\text{ W}$ ; $f = 1\text{ kHz}$                                 |                 | 0.005  |           | %                |
|                                                          |                                                                              | $P_O = 0.1\text{ to }50\text{ W}$ ; $f = 20\text{ Hz to }20\text{ kHz}$ |                 |        | 0.1       | %                |
|                                                          |                                                                              | $V_S = \pm 27\text{ V}$ , $R_L = 4\ \Omega$                             |                 |        |           |                  |
|                                                          |                                                                              | $P_O = 5\text{ W}$ ; $f = 1\text{ kHz}$                                 |                 | 0.01   |           | %                |
|                                                          |                                                                              | $P_O = 0.1\text{ to }50\text{ W}$ ; $f = 20\text{ Hz to }20\text{ kHz}$ |                 |        | 0.1       | %                |
| SR                                                       | Slew rate                                                                    |                                                                         | 7               | 10     |           | V/ $\mu\text{s}$ |
| $G_V$                                                    | Open loop voltage gain                                                       |                                                                         |                 | 80     |           | dB               |
|                                                          | Closed loop voltage gain                                                     |                                                                         | 24              | 30     | 40        | dB               |
| $e_N$                                                    | Total input noise                                                            | A = curve<br>$f = 20\text{ Hz to }20\text{ kHz}$                        |                 | 1<br>2 | 5         | $\mu\text{V}$    |
| $f_L, f_H$                                               | Frequency response (-3 dB)                                                   | $P_O = 1\text{ W}$                                                      | 20 Hz to 20 kHz |        |           |                  |
| $R_i$                                                    | Input resistance                                                             |                                                                         | 100             |        |           | k $\Omega$       |
| SVR                                                      | Supply voltage rejection                                                     | $f = 100\text{ Hz}$ ; Vripple = 0.5 Vrms                                | 60              | 75     |           | dB               |
| $T_S$                                                    | Thermal shutdown                                                             |                                                                         |                 | 145    |           | $^\circ\text{C}$ |
| <b>Stand-by function (Ref: <math>-V_S</math> or GND)</b> |                                                                              |                                                                         |                 |        |           |                  |
| $V_{ST\text{ on}}$                                       | Stand-by on threshold                                                        |                                                                         |                 |        | 1.5       | V                |
| $V_{ST\text{ off}}$                                      | Stand-by off threshold                                                       |                                                                         | 3.5             |        |           | V                |
| $ATT_{\text{st-by}}$                                     | Stand-by attenuation                                                         |                                                                         | 70              | 90     |           | dB               |
| $I_q\text{ st-by}$                                       | Quiescent current @ Stand-by                                                 |                                                                         |                 | 1      | 3         | mA               |
| <b>Mute function (Ref: <math>-V_S</math> or GND)</b>     |                                                                              |                                                                         |                 |        |           |                  |

| Symbol       | Parameter          | Test condition | Min. | Typ. | Max. | Unit |
|--------------|--------------------|----------------|------|------|------|------|
| $V_{Mon}$    | Mute on threshold  |                |      |      | 1.5  | V    |
| $V_{Moff}$   | Mute off threshold |                | 3.5  |      |      | V    |
| $ATT_{mute}$ | Mute attenuation   |                | 60   | 80   |      | dB   |

1. **MUSIC POWER CONCEPT** - **MUSIC POWER** is the maximal power which the amplifier is capable of producing across the rated load resistance (regardless of non linearity) 1 sec after the application of a sinusoidal input signal of frequency 1 kHz.
2. Limited by the max. allowable current.
3. Tested with optimized application board (see [Figure 4](#)).

## 6 PCB and components

**Figure 4.** PCB and components layout of the circuit of figure below. (1:1 scale)



*Note:* The Stand-by and Mute functions can be referred either to GND or -VS.  
On the PCB is possible to set both the configuration through the jumper J1.

## 7 Application suggestion

The recommended values of the external components are those shown on the application circuit of [Figure 1](#). Different values can be used; the following table can help the designer.

| COMPONENTS        | SUGGESTED VALUE | PURPOSE                                      | LARGER THAN SUGGESTED    | SMALLER THAN SUGGESTED               |
|-------------------|-----------------|----------------------------------------------|--------------------------|--------------------------------------|
| R1 <sup>(1)</sup> | 22 kΩ           | INPUT RESISTANCE                             | INCREASE INPUT IMPEDANCE | DECREASE INPUT IMPEDANCE             |
| R2                | 680 Ω           | CLOSED LOOP GAIN SET TO 30 dB <sup>(2)</sup> | DECREASE OF GAIN         | INCREASE OF GAIN                     |
| R3 <sup>(1)</sup> | 22 kΩ           |                                              | INCREASE OF GAIN         | DECREASE OF GAIN                     |
| R4                | 22 kΩ           | ST-BYTIME CONSTANT                           | LARGERST-BY ON/OFF TIME  | SMALLER ST-BY ON/OFF TIME; POP NOISE |
| R5                | 10 kΩ           | MUTE TIME CONSTANT                           | LARGER MUTE ON/OFF TIME  | SMALLER MUTE ON/OFF TIME             |
| C1                | 0.47 μF         | INPUT DC DECOUPLING                          |                          | HIGHER LOW FREQUENCY CUTOFF          |
| C2                | 22 μF           | FEEDBACK DC DECOUPLING                       |                          | HIGHER LOW FREQUENCY CUTOFF          |
| C3                | 10 μF           | MUTETIME CONSTANT                            | LARGER MUTE ON/OFF TIME  | SMALLER MUTE ON/OFF TIME             |
| C4                | 10 μF           | ST-BYTIME CONSTANT                           | LARGERST-BY ON/OFF TIME  | SMALLERST-BY ON/OFF TIME; POP NOISE  |
| C5                | 22 μF           | BOOT STRAPPING                               |                          | SIGNAL DEGRADATION AT LOW FREQUENCY  |
| C6, C8            | 1000 μF         | SUPPLY VOLTAGE BYPASS                        |                          | DANGER OF OSCILLATION                |
| C7, C9            | 0.1 μF          | SUPPLY VOLTAGE BYPASS                        |                          | DANGER OF OSCILLATION                |

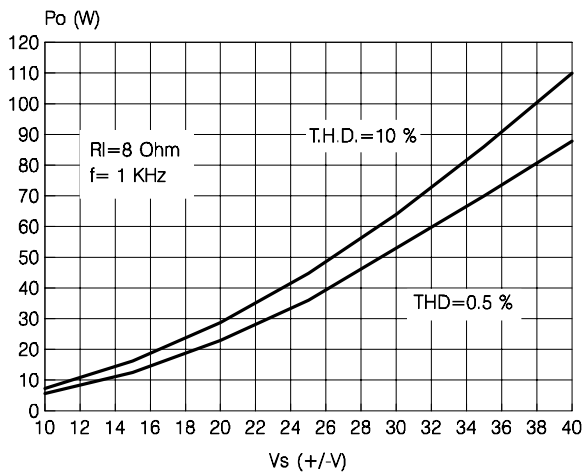
1. R1= R3 for pop optimization.

2. Closed loop gain has to be 24 dB.

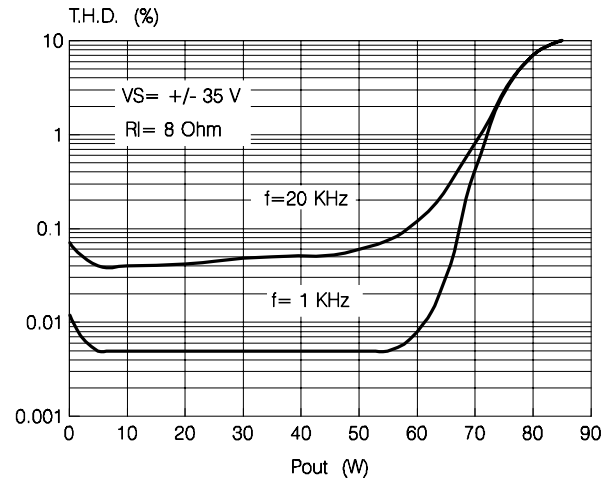
## 8 Typical characteristics

Application circuit of fig 1 unless otherwise specified.

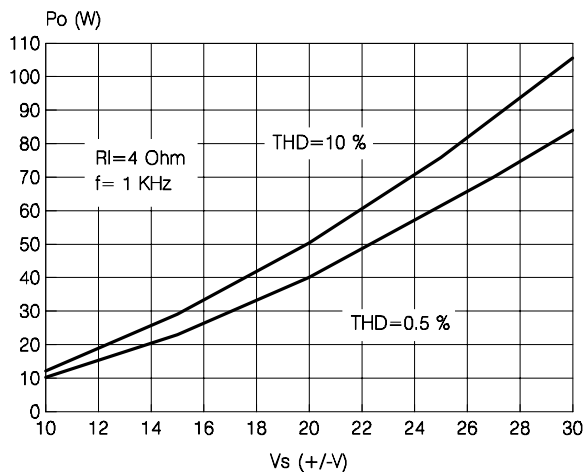
**Figure 5. Output power vs. supply voltage ( $R_L = 8 \Omega$ )**



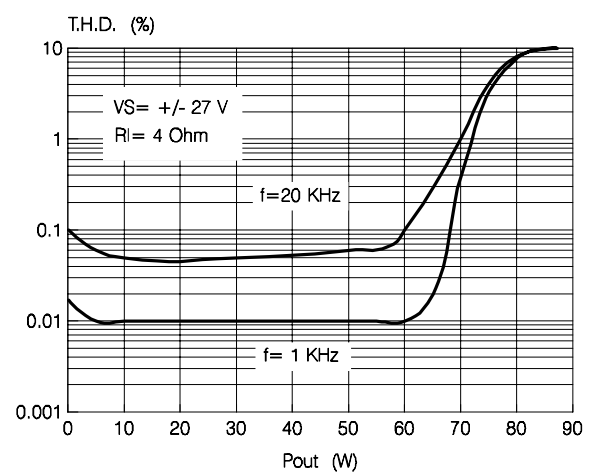
**Figure 6. Distortion vs. output power ( $R_L = 8 \Omega$ )**



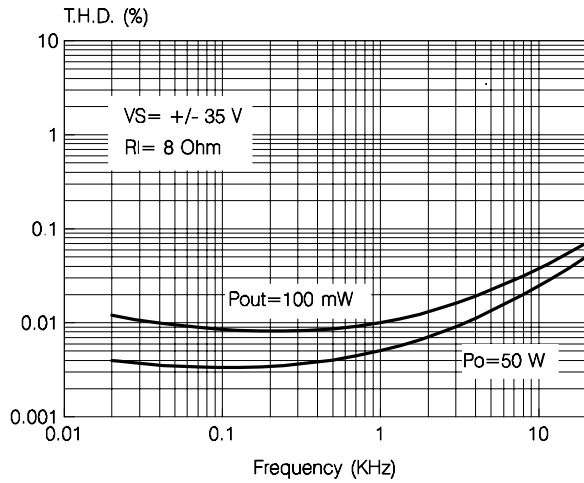
**Figure 7. Output power vs. supply voltage ( $R_L = 4 \Omega$ )**



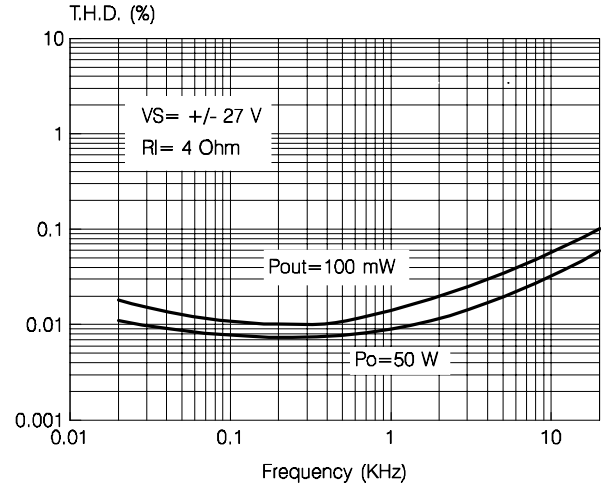
**Figure 8. Distortion vs. output power ( $R_L = 4 \Omega$ )**



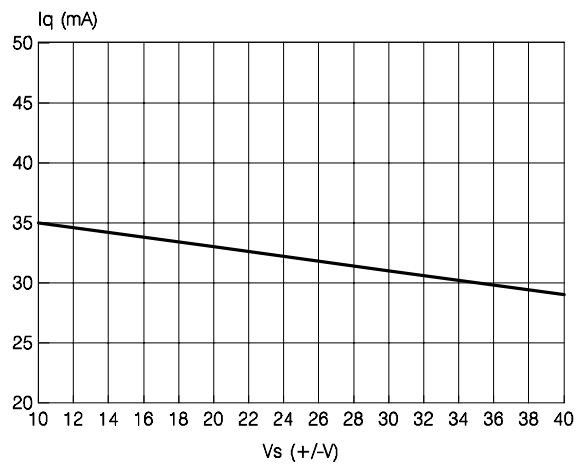
**Figure 9. Distortion vs. frequency (RI = 8 Ω)**



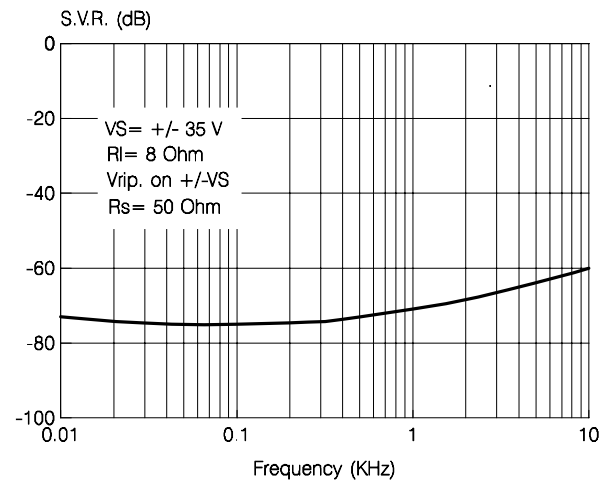
**Figure 10. Distortion vs. frequency (RI = 4 Ω)**



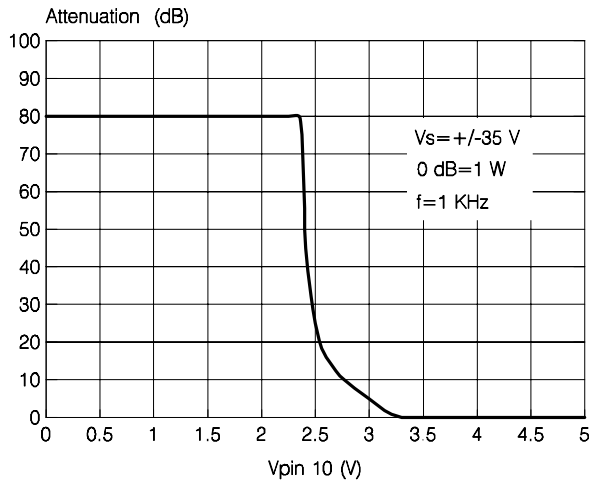
**Figure 11. Quiescent current vs. supply voltage**



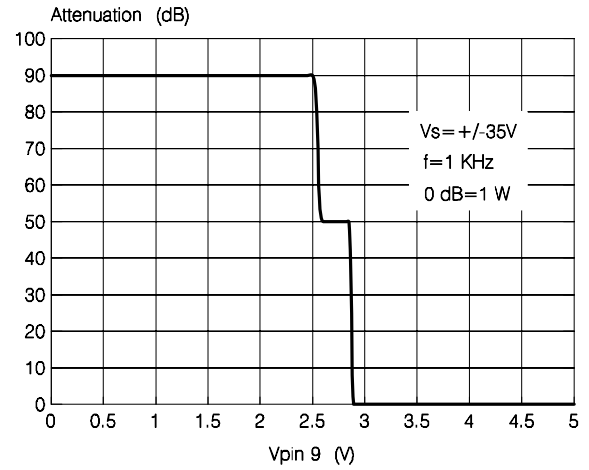
**Figure 12. Supply voltage rejection vs. frequency**



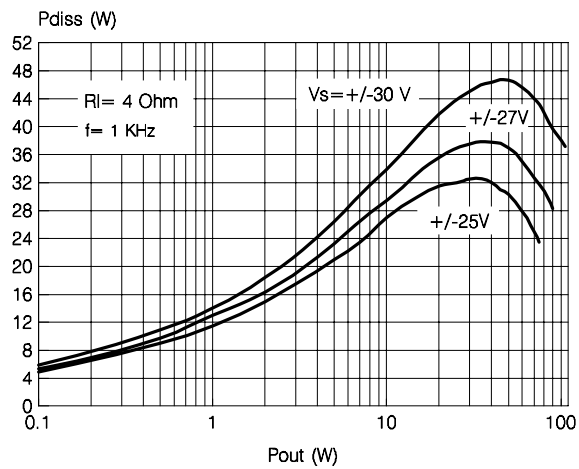
**Figure 13. Mute attenuation vs.  $V_{pin10}$**



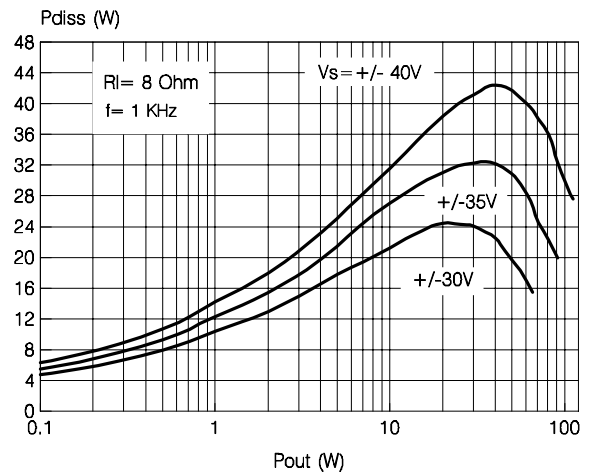
**Figure 14. St-by attenuation vs.  $V_{pin9}$**



**Figure 15. Power dissipation vs. output power ( $R_L = 4 \Omega$ )**



**Figure 16. Power dissipation vs. output power ( $R_L = 8 \Omega$ )**



## 9 Introduction

In consumer electronics, an increasing demand has arisen for very high power monolithic audio amplifiers able to match, with a low cost the performance obtained from the best discrete designs.

The task of realizing this linear integrated circuit in conventional bipolar technology is made extremely difficult by the occurrence of 2<sup>nd</sup> breakdown phenomenon. It limits the safe operating area (SOA) of the power devices, and as a consequence, the maximum attainable output power, especially in presence of highly reactive loads.

Moreover, full exploitation of the SOA translates into a substantial increase in circuit and layout complexity due to the need for sophisticated protection circuits.

To overcome these substantial drawbacks, the use of power MOS devices, which are immune from secondary breakdown is highly desirable.

The device described has therefore been developed in a mixed bipolar-MOS high voltage technology called BCD 100.

### 9.1 Output stage

The main design task one is confronted with while developing an integrated circuit as a power operational amplifier, independently of the technology used, is that of realizing the output stage.

The solution shown as a principle schematic by [Figure 17](#) represents the DMOS unity-gain output buffer of the TDA7294.

This large-signal, high-power buffer must be capable of handling extremely high current and voltage levels while maintaining acceptably low harmonic distortion and good behaviour over frequency response; moreover, an accurate control of quiescent current is required.

A local linearizing feedback, provided by differential amplifier A, is used to fulfil the above requirements, allowing a simple and effective quiescent current setting.

Proper biasing of the power output transistors alone is however not enough to guarantee the absence of crossover distortion.

While a linearization of the DC transfer characteristic of the stage is obtained, the dynamic behaviour of the system must be taken into account.

A significant aid in keeping the distortion contributed by the final stage as low as possible is provided by the compensation scheme, which exploits the direct connection of the Miller capacitor at the amplifier's output to introduce a local AC feedback path enclosing the output stage itself.

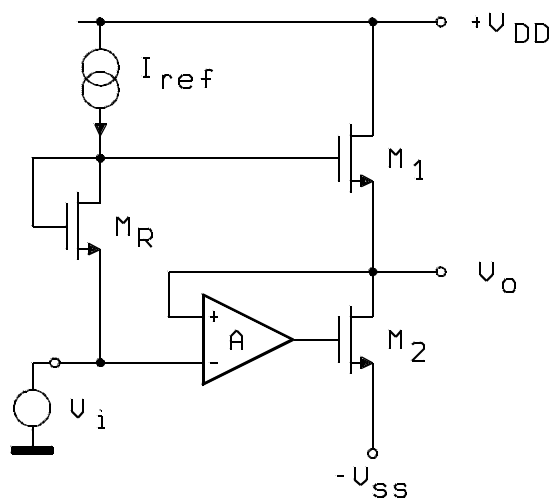
### 9.2 Protections

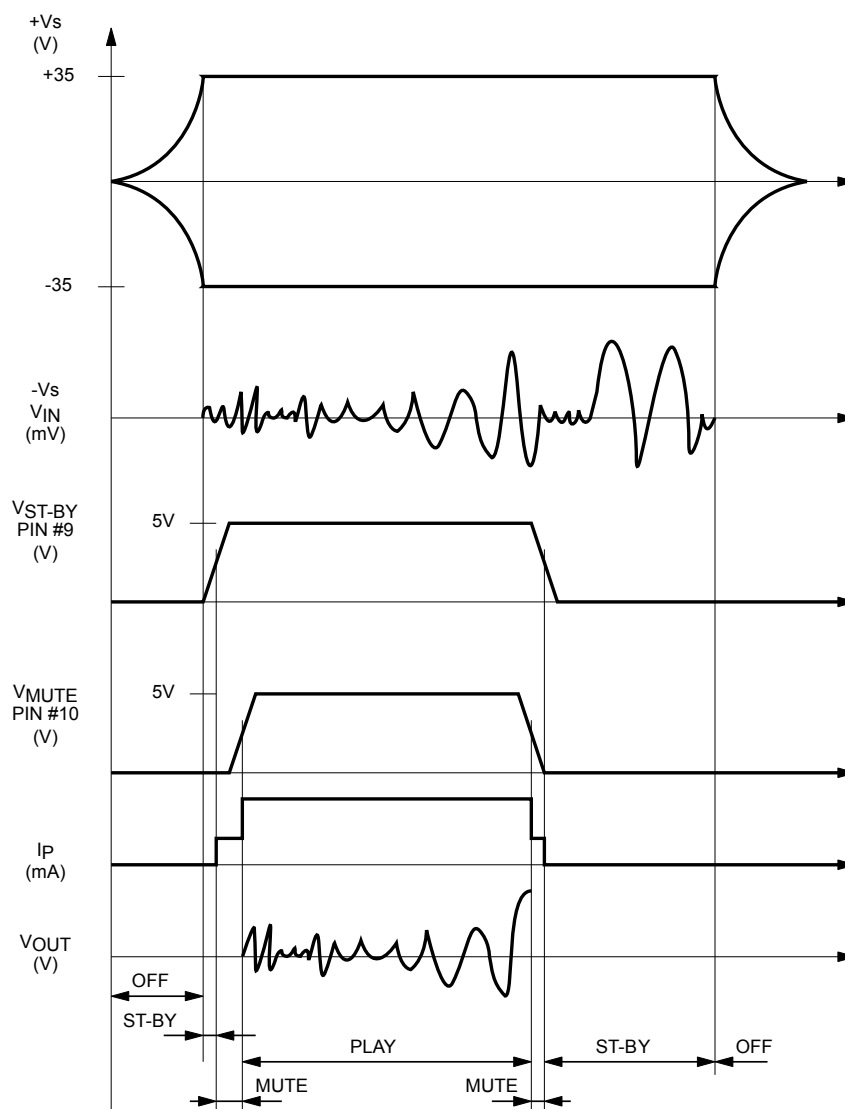
In designing a power IC, particular attention must be reserved to the circuits devoted to protection of the device from short circuit or overload conditions.

Due to the absence of the 2<sup>nd</sup> breakdown phenomenon, the SOA of the power DMOS transistors is delimited only by a maximum dissipation curve dependent on the duration of the applied stimulus.

In order to fully exploit the capabilities of the power transistors, the protection scheme implemented in this device combines a conventional SOA protection circuit with a novel local temperature sensing technique which "dynamically" controls the maximum dissipation.

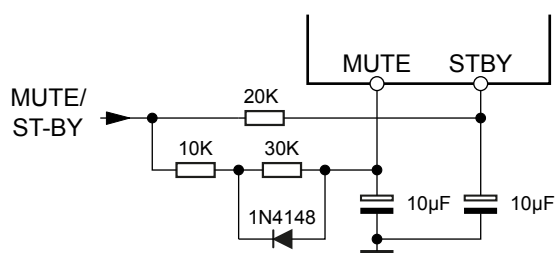
**Figure 17. Principle schematic of a DMOS unity-gain buffer**



**Figure 18. Turn ON/OFF suggested sequence**


In addition to the overload protection described above, the device features a thermal shutdown circuit which initially puts the device into a muting state (@  $T_j = 145^\circ\text{C}$ ) and then into stand-by (@  $T_j = 150^\circ\text{C}$ ).

Full protection against electrostatic discharges on every pin is included.

**Figure 19. Single signal ST-BY/MUTE control circuit**


### 9.3 Other features

The device is provided with both stand-by and mute functions, independently driven by two CMOS logic compatible input pins.

The circuits dedicated to the switching on and off of the amplifier have been carefully optimized to avoid any kind of uncontrolled audible transient at the output.

The sequence that we recommend during the ON/OFF transients is shown by [Figure 18](#).

The application of [Figure 19](#) shows the possibility of using only one command for both st-by and mute functions. On both the pins, the maximum applicable range corresponds to the operating supply voltage.

## 10 Application information

### High-efficiency

Constraints of implementing high power solutions are the power dissipation and the size of the power supply. These are both due to the low efficiency of conventional AB class amplifier approaches.

Here below (Figure 18) is described a circuit proposal for a high efficiency amplifier which can be adopted for both HI-FI and CAR-RADIO applications.

The TDA7294 is a monolithic MOS power amplifier which can be operated at 80 V supply voltage (100 V with no signal applied) while delivering output currents up to  $\pm 10$  A.

This allows the use of this device as a very high power amplifier (up to 180 W as peak power with T.H.D. = 10 % and  $R_L = 4$  Ohm); the only drawback is the power dissipation, hardly manageable in the above power range.

Figure 22 shows the power dissipation versus output power curve for a class AB amplifier, compared with a high efficiency one.

In order to dimension the heatsink (and the power supply), a generally used average output power value is one tenth of the maximum output power at T.H.D. = 10 %.

From Figure 22, where the maximum power is around 200 W, we get an average of 20 W, in this condition, for a class AB amplifier the average power dissipation is equal to 65 W.

The typical junction-to-case thermal resistance of the TDA7294 is 1 °C/W (max= 1.5 °C/W). To avoid that, in worst case conditions, the chip temperature exceeds 150 °C, the thermal resistance of the heatsink must be 0.038 °C/W (@ max ambient temperature of 50 °C).

As the above value is practically unreachable; a high efficiency system is needed in those cases where the continuous RMS output power is higher than 50-60 W.

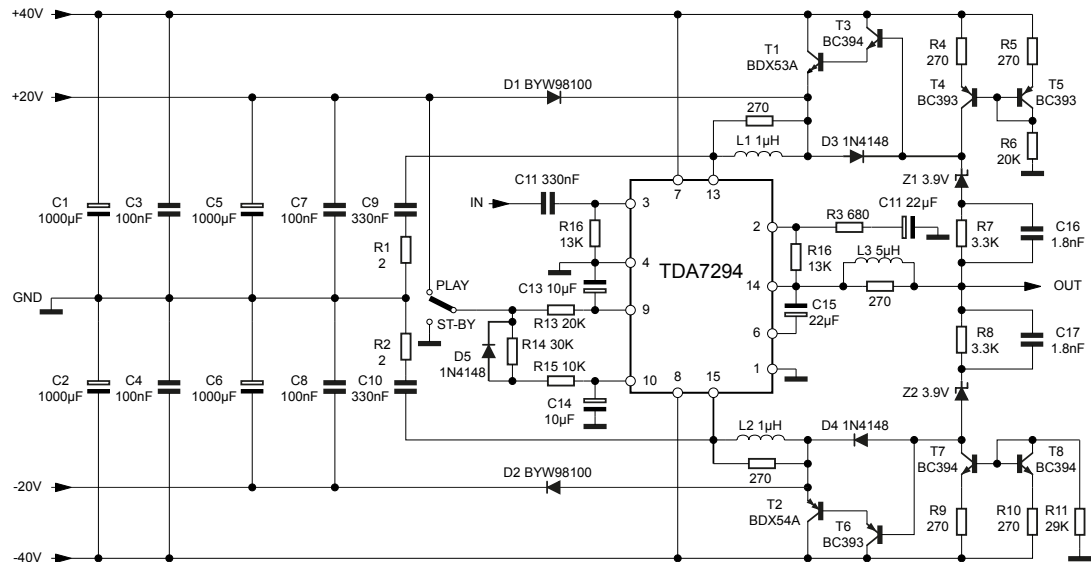
The TDA7294 was designed to work also in higher efficiency way.

For this reason there are four power supply pins: intended for the signal part and two for the power part.

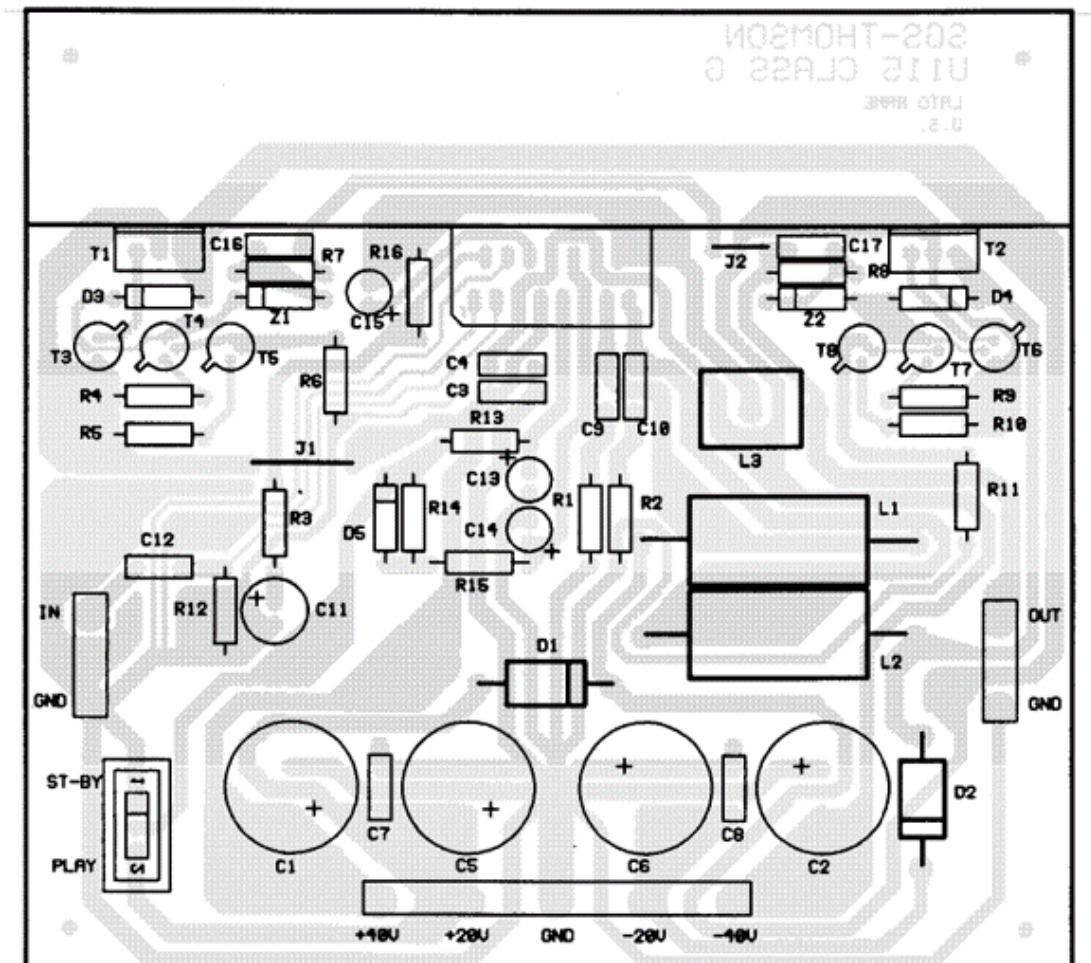
T1 and T2 are two power transistors that only operate when the output power reaches a certain threshold (e.g. 20 W). If the output power increases, these transistors are switched on during the portion of the signal where more output voltage swing is needed, thus "bootstrapping" the power supply pins (#13 and #15).

The current generators formed by T4, T7, zener diodes Z1, Z2 and resistors R7, R8 define the minimum drop across the power MOS transistors of the TDA7294. L1, L2, L3 and the snubbers C9, R1 and C10, R2 stabilize the loops formed by the "bootstrap" circuits and the output stage of the TDA7294.

**Figure 20. High efficiency application circuit**



**Figure 21. P.C.B. and components layout of the circuit of figure 18 (1:1 scale)**



In [Figure 23](#), [Figure 24](#) the performances of the system in terms of distortion and output power at various frequencies (measured on PCB shown in [Figure 21](#)) are displayed.

The output power that the TDA7294 in highefficiency application is able to supply at  $V_s = +40\text{ V} / +20\text{ V} / -20\text{ V} / -40\text{ V}$ ;  $f = 1\text{ kHz}$  is:

- $P_{out} = 150\text{ W}$  @ T.H.D. = 10 % with  $R_L = 4\ \Omega$
- $P_{out} = 120\text{ W}$  @ T.H.D. = 1 % with  $R_L = 4\ \Omega$
- $P_{out} = 100\text{ W}$  @ T.H.D. = 10 % with  $R_L = 8\ \Omega$
- $P_{out} = 80\text{ W}$  @ T.H.D. = 10 % with  $R_L = 8\ \Omega$

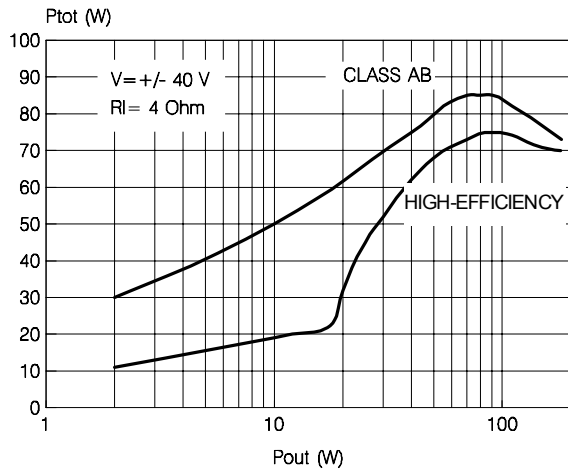
Results from efficiency measurements (4 and 8  $\Omega$  loads,  $V_s = \pm 40\text{ V}$ ) are shown by figures [Figure 25](#) and [Figure 26](#). We have 3 curves: total power dissipation, power dissipation of the TDA7294 and power dissipation of the darlington.

By considering again a maximum average output power (music signal) of 20 W, in case of the high efficiency application, the thermal resistance value needed from the heatsink is  $2.2\text{ }^\circ\text{C} / \text{W}$  ( $V_s = \pm 40\text{ V}$  and  $R_L = 4\ \Omega$ ).

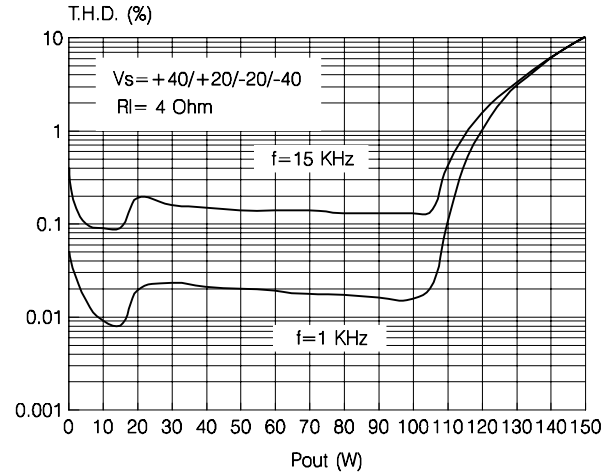
All components (TDA7294 and power transistors T1 and T2) can be placed on a  $1.5\text{ }^\circ\text{C} / \text{W}$  heatsink, with the power darlington electrically insulated from the heatsink.

Since the total power dissipation is less than that of a usual class AB amplifier, additional cost savings can be obtained while optimizing the power supply, even with a high headroom.

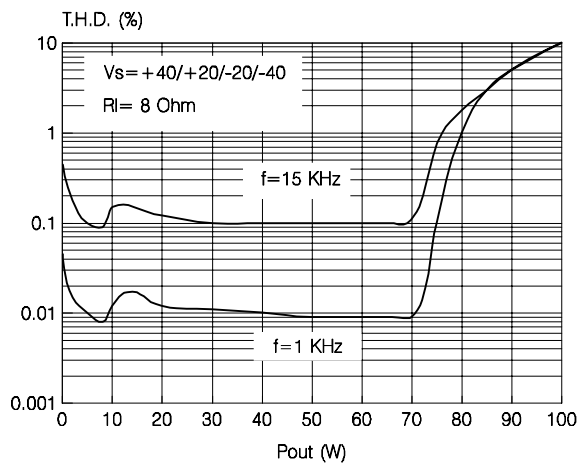
**Figure 22. Power dissipation vs. output power (RI = 4 Ω)**



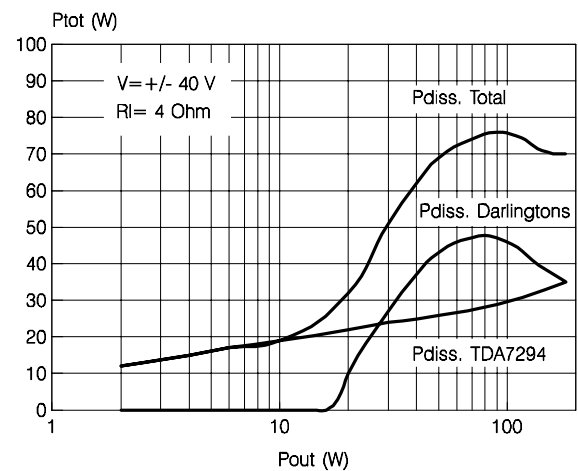
**Figure 23. Distortion vs. output power (RI = 4 Ω)**



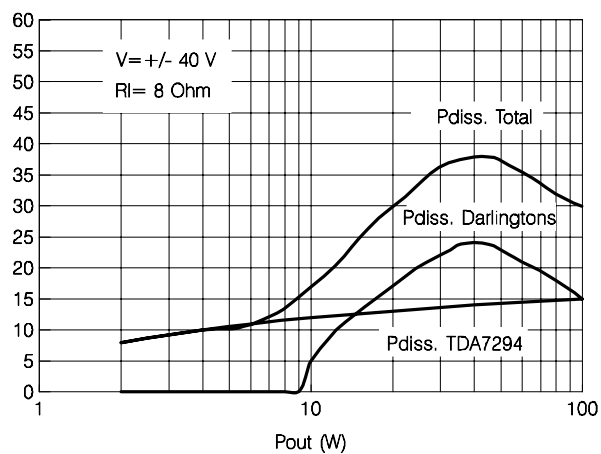
**Figure 24. Distortion vs. output power (RI = 8 Ω)**



**Figure 25. Power dissipation vs. output power (RI = 4 Ω)**



**Figure 26. Power dissipation vs. output power ( $R_L = 8\ \Omega$ )**



## 11 Bridge application

Another application suggestion is the BRIDGE configuration, where two TDA7294 are used, as shown by the schematic diagram of Figure 27.

In this application, the value of the load must not be lower than  $8\ \Omega$  for dissipation and current capability reasons.

A suitable field of application includes HI-FI/TV subwoofers realizations.

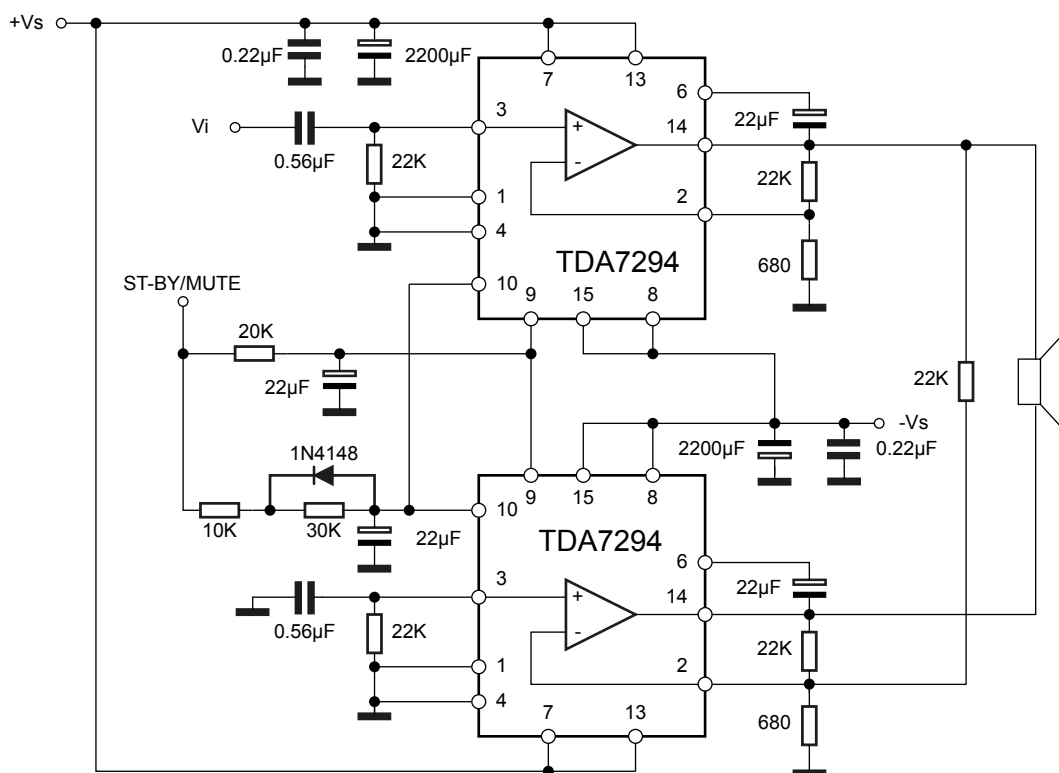
The main advantages offered by this solution are:

- High power performances with limited supply voltage level.
- Considerably high output power even with high load values (i.e.  $16\ \Omega$ ).

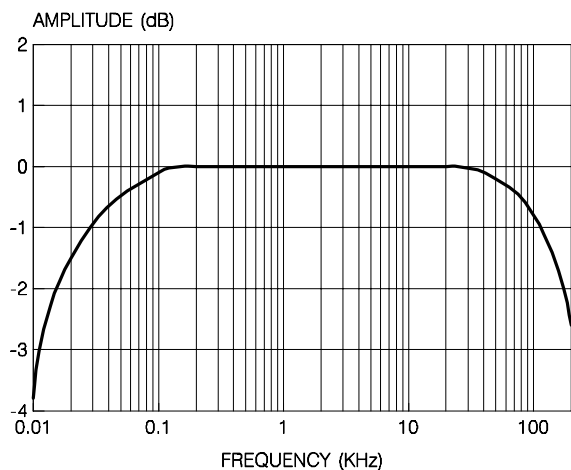
The characteristics shown by Figure 29 and Figure 30, measured with loads respectively  $8\ \Omega$  and  $16\ \Omega$ .

With  $R_L = 8\ \Omega$ ,  $V_s = \pm 25\text{ V}$  the maximum output power obtainable is 150 W, while with  $R_L = 16\ \Omega$ ,  $V_s = \pm 35\text{ V}$  the maximum  $P_{out}$  is 170 W.

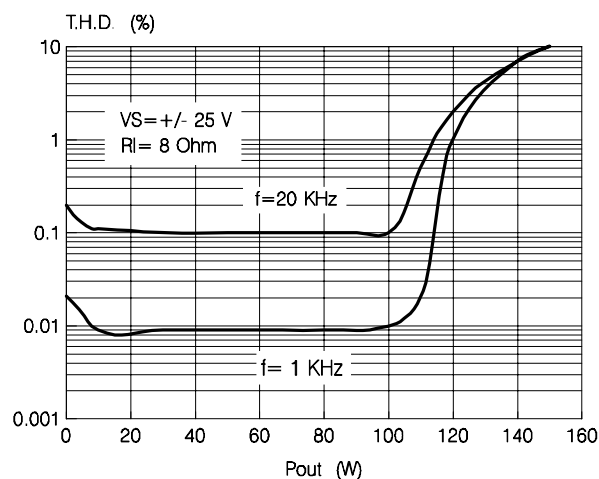
**Figure 27. Bridge application circuit**



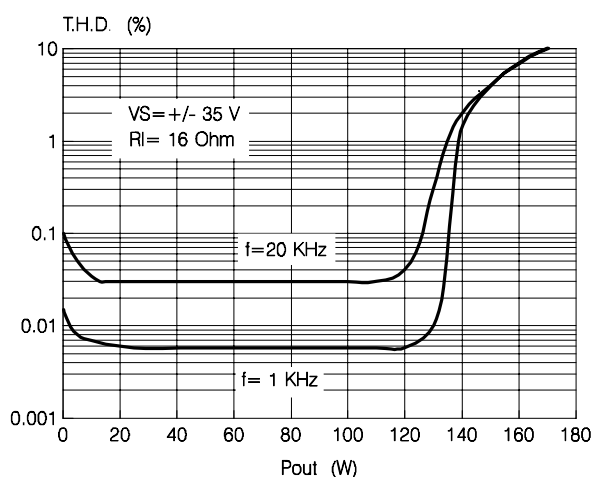
**Figure 28. Frequency response of the bridge application**



**Figure 29. Distortion vs. output power (RI = 8 Ω)**



**Figure 30. Distortion vs. output power (RI = 16 Ω)**



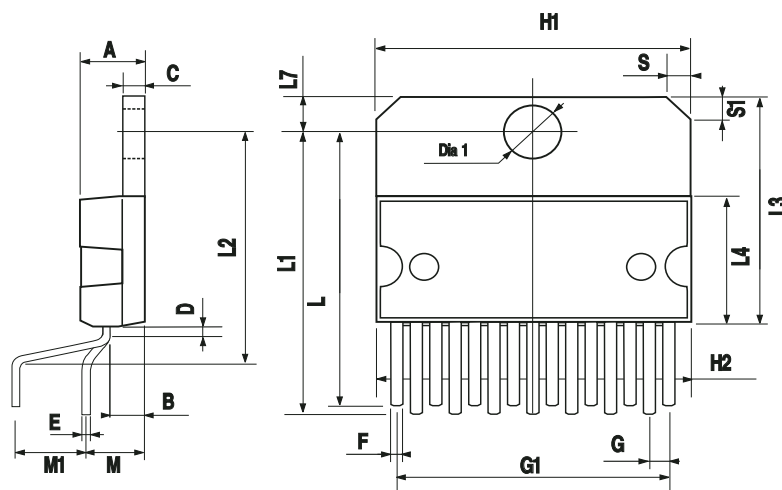
## 12 Package information

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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

## 12.1 Multiwatt15 V package information

**Figure 31. Multiwatt15 V package outline**

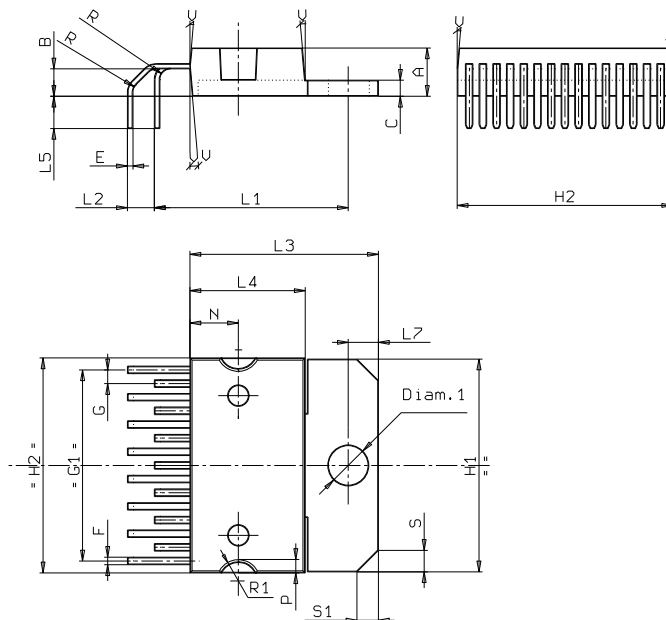


**Table 4. Multiwatt15 V mechanical data**

| Dim.    | mm    |       |       |
|---------|-------|-------|-------|
|         | Min.  | Typ.  | Max.  |
| A       |       |       | 5     |
| B       |       |       | 2.65  |
| C       |       |       | 1.6   |
| D       |       | 1     |       |
| E       | 0.49  |       | 0.55  |
| F       | 0.66  |       | 0.75  |
| G       | 1.02  | 1.27  | 1.52  |
| G1      | 17.53 | 17.78 | 18.03 |
| H1      | 19.6  |       |       |
| H2      |       |       | 20.2  |
| L       | 21.9  | 22.2  | 22.5  |
| L1      | 21.7  | 22.1  | 22.5  |
| L2      | 17.65 |       | 18.1  |
| L3      | 17.25 | 17.5  | 17.75 |
| L4      | 10.3  | 10.7  | 10.9  |
| L7      | 2.65  |       | 2.9   |
| M       | 4.25  | 4.55  | 4.85  |
| M1      | 4.63  | 5.08  | 5.53  |
| S       | 1.9   |       | 2.6   |
| S1      | 1.9   |       | 2.6   |
| Diam. 1 | 3.65  |       | 3.85  |

## 12.2 Multiwatt15 H package information

**Figure 32. Multiwatt15 H package outline**



**Table 5. Multiwatt15 H mechanical data**

| Dim.    | mm    |       |       |
|---------|-------|-------|-------|
|         | Min.  | Typ.  | Max.  |
| A       |       |       | 5.00  |
| B       |       |       | 2.65  |
| C       |       |       | 1.60  |
| E       | 0.49  |       | 0.55  |
| F       | 0.66  |       | 0.75  |
| G       | 1.02  | 1.27  | 1.52  |
| G1      | 17.53 | 17.78 | 18.03 |
| H1      | 19.60 |       | 20.20 |
| H2      | 19.60 |       | 20.20 |
| L1      | 17.80 | 18.0  | 18.20 |
| L2      | 2.30  | 2.50  | 2.80  |
| L3      | 17.25 | 17.50 | 17.75 |
| L4      | 10.3  | 10.70 | 10.90 |
| L5      | 2.70  | 3.00  | 3.30  |
| L7      | 2.65  |       | 2.90  |
| R       |       | 1.50  |       |
| S       | 1.90  |       | 2.60  |
| S1      | 1.90  |       | 2.60  |
| Diam. 1 | 3.65  |       | 3.85  |

## Revision history

**Table 6. Document revision history**

| Date        | Version | Changes                                                                 |
|-------------|---------|-------------------------------------------------------------------------|
| Apr-2003    | 7       | First issue in EDOCS DMS.                                               |
| 31-Jul-2020 | 8       | Updated <a href="#">Section 12.2</a> Multiwatt15 H package information. |

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